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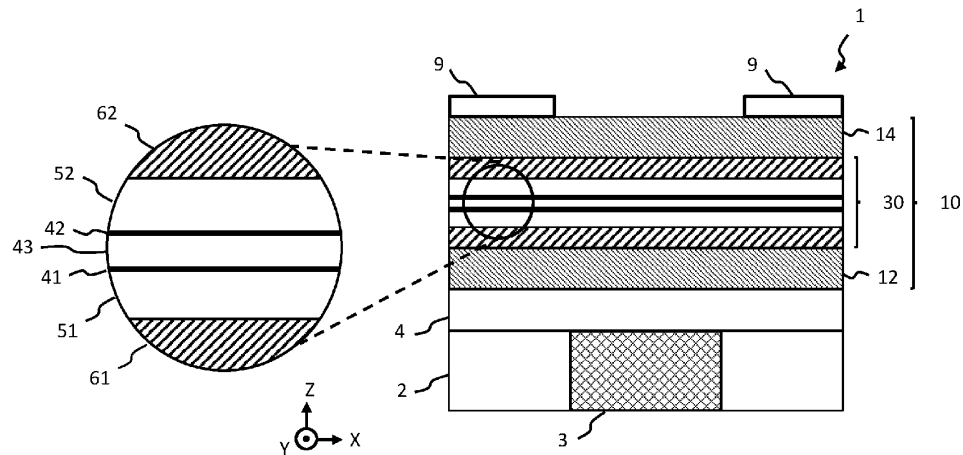


Fig. 1

(57) Abstract: A device (1) for emitting light, the device (1) comprising: a substrate (2); a base layer (4) arranged on the substrate (2); a diode layer structure (10) arranged on the base layer (4), the diode layer structure (10) comprising a quantum well layer structure (30) sandwiched between an n-doped semiconductor layer (12) and a p-doped semiconductor layer (14); the quantum well layer structure (30) comprising a first (41) and second (42) quantum well, a first (51) and a second (52) proximal barrier layer, and a first (61) and a second (62) distal barrier layer, wherein the first (41) and second (42) quantum wells and the first (51) and second (52) proximal barrier layers are sandwiched between the first (61) and second (62) distal barrier layers

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